

1. Scope :

This specification applies to N/P silicon zener diode chips,
Device NO. SD-40660G

2. Structure :

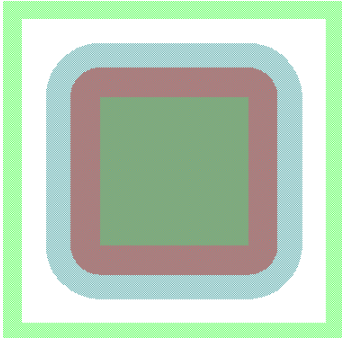
- 2-1. Planar type : N/P Diode
- 2-2. Electrodes :
 - Top side : Gold pad.
 - Back side : Gold layer.

3. Size :

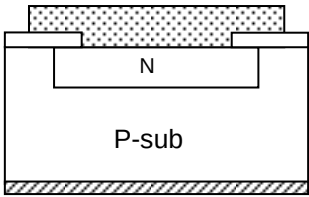
- 3-1. ^{※1} Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
- 3-2. Chip thickness : 3.3 ± 0.6 mils (0.085 ± 0.015 mm)
- 3-3. Active area : 4.1 mils x 4.1 mils (0.105 mm x 0.105 mm).
- 3-4. ^{※2} Bonding pad : 4.8 mils x 4.8 mils (0.122 mm x 0.122 mm).
- 3-5. Pattern drawing : Refer to the attached drawing.
 - ^{※1} Including scribing line. The chip size is about (0.150±0.015)²mm² after dicing.
 - ^{※2} The bonding pad dimension is about (0.122±0.005)²mm².

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	IR	VR=4V Ee=0mW/cm ²			100	nA
Zener Voltage	Vz	Iz=5mA Ee=0mW/cm ²	5.7		6.7	V
Forward Voltage	Vf	IF=20mA Ee=0mW/cm ²			1.2	V



Cathode



Anode

